2SA1830 : PNPEpitaxial Planar Silicon Transistor 2SC4734 ; NPN Triple Diffused Planar Silicon Transistor



2SA1830/2SC4734

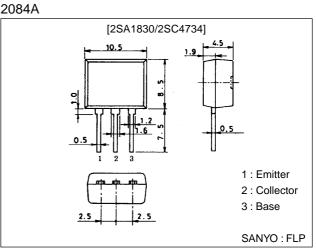
High-Voltage Driver Applications

Features

- · Large current capacity ($I_C=2A$).
- \cdot High breakdown voltage (V_{CEO}{\geq}400V).
- Possible to offer the 2SA1830/2SC4734 devices in a tape reel packaging, which facilitates automatic insertion.

Package Dimensions

unit:mm



():2SA1830

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		(-)400	V
Collector-to-Emitter Voltage	VCEO		(–)400	V
Emitter-to-Base Voltage	V _{EBO}		(–)5	V
Collector Current	IC		(–)2	A
Collector Current (Pulse)	ICP		(-)4	A
Collector Dissipation	PC		1.5	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =(-)300V, I _E =0			(–)1.0	μA
Emitter Cutoff Current	IEBO	V _{EB} =(-)4V, I _C =0			(–)1.0	μA
DC Current Gain	hFE	V _{CE} =(-)10V, I _C =(-)100mA	40*		200*	
Gain-Bandwidth Product	fT	V _{CE} =(-)10V, I _C =(-)100mA		(40)60		MHz
Output Capacitance	Cob	V _{CB} =(-)30V, f=1MHz		(25)15		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =(-)500mA, I _B =(-)50mA			(–)1.0	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =(–)500mA, I _B =(–)50mA			(–)1.0	V

 \ast : The 2SA1830/2SC4734 are classified by 100mA h_{FE} as follows :

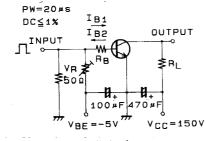
40 C 80 60 D 120 100 E 200

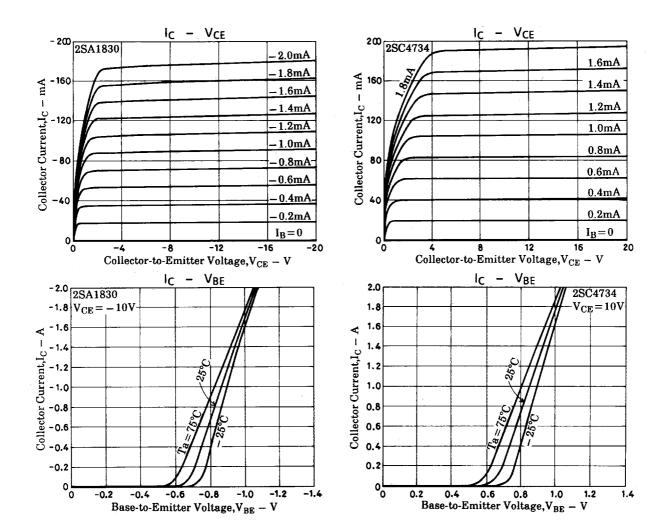
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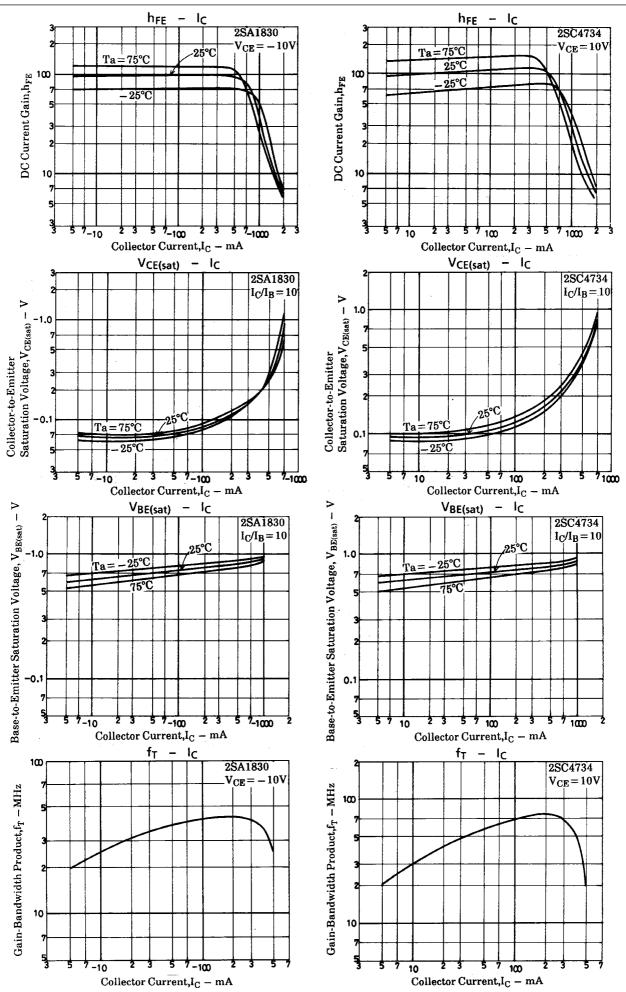
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Parameter	Symbol	Conditions		Ratings		
			min	typ	max	Unit
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =(-)10µA, I _E =0	(-)400			V
Collector-to-Emitter Breakdown Voltage	V _(BR) CEO	I _C =(−)1mA, R _{BE} =∞	(–)400			V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	I _E =(-)10μΑ, I _C =0	(–)5			V
Turn-ON Time	ton	See specified Test Circuit		(0.12)		μs
				0.085		μs
Storage Time	^t stg	See specified Test CIrcuit		(3.0)		μs
				4.0		μs
Fall Time	t _f	See specified Test Circuit		(0.3)		μs
				0.6		μs

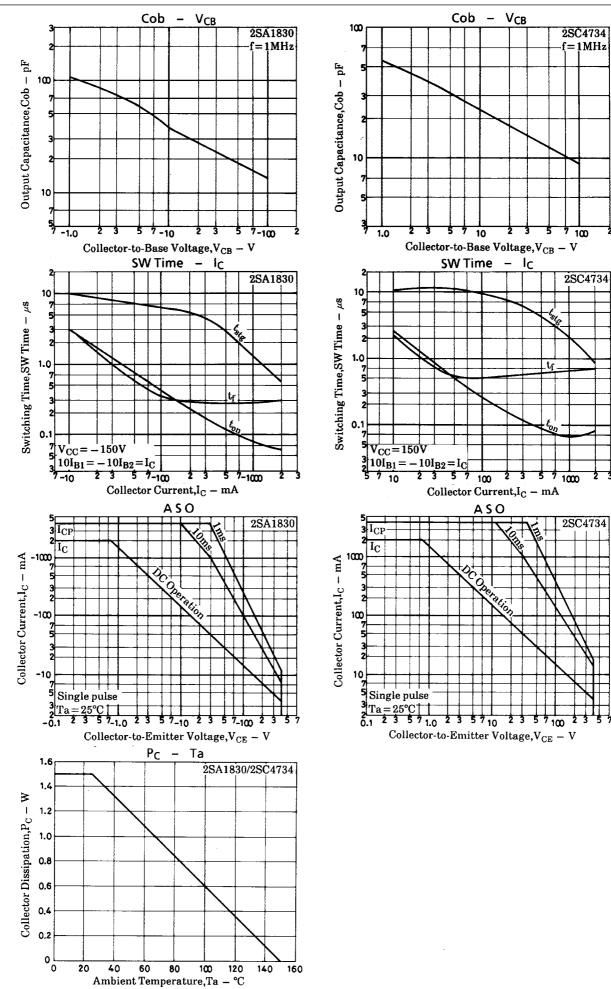
Switching Time Test Circuit







2SA1830/2SC4734



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